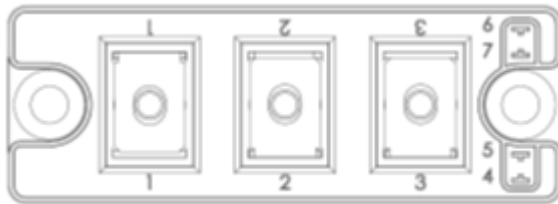
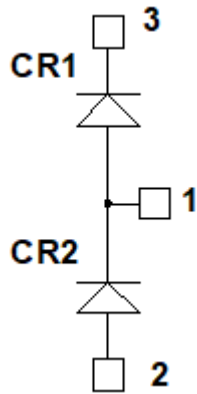


## MSCDC200A120D1PAG Phase leg SiC diodes Power Module

### 1 Product Overview

This section shows the product overview for the MSCDC200A120D1PAG device.



All ratings at  $T_j = 25^\circ\text{C}$ , unless otherwise specified.

**Caution:** These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

## 1.1 Features

The following are key features of the MSCDC200A120D1PAG device:

- Silicon Carbide (SiC) Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on VF
- M5 power connectors
- Aluminum nitride (AlN) substrate for improved thermal performance

## 1.2 Benefits

The following are benefits of the MSCDC200A120D1PAG device:

- Stable temperature behavior
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

## 1.3 Applications

The MSCDC200A120D1PAG device is designed for the following applications:

- Uninterruptible power supply (UPS)
- Switched mode power supply
- Welding converters
- Motor control

## 2 Electrical Specifications

This section shows the electrical specifications for the MSCDC200A120D1PAG device.

### 2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode for the MSCDC200A120D1PAG device.

**Table 1 • Absolute Maximum Ratings**

Symbol	Parameter	Maximum Ratings	Unit
$V_{RRM}$	Repetitive peak reverse voltage	1200	V
$I_F$	DC forward current	$T_C = 95\text{ }^\circ\text{C}$ 200	A

The following table shows the thermal and package characteristics of the MSCDC200A120D1PAG.

**Table 2 • Thermal and Package Characteristics**

Symbol	Characteristic	Min	Max	Unit		
$V_{ISOL}$	RMS isolation voltage, any terminal to case $t = 1$ minute, 50 Hz/60 Hz	4000		V		
$T_J$	Operating junction temperature range	-40	175	$^\circ\text{C}$		
$T_{JOP}$	Recommended junction temperature under switching conditions	-40	$T_{Jmax} - 25$			
$T_{STG}$	Storage temperature range	-40	125			
$T_C$	Operating case temperature	-40	125			
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight			160	g	

### 2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC200A120D1PAG.

**Table 3 • Electrical Characteristics Per Diode**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_F$	Diode forward voltage	$I_F = 200\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	1.5	1.8	V
			$T_J = 175\text{ }^\circ\text{C}$	2.1		
$I_{RM}$	Reverse leakage current	$V_R = 1200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	60	800	$\mu\text{A}$
			$T_J = 175\text{ }^\circ\text{C}$	1000		
$Q_C$	Total capacitive charge	$V_R = 600\text{ V}$		896		nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400\text{ V}$		984		pF
		$f = 1\text{ MHz}, V_R = 800\text{ V}$		728		
$R_{thJC}$	Junction-to-case thermal resistance				0.16	$^\circ\text{C/W}$

## 2.3 Performance Curves

This section shows the typical performance curves for the MSCDC200A120D1PAG device.

Figure 1 • Maximum Transient Thermal Impedance

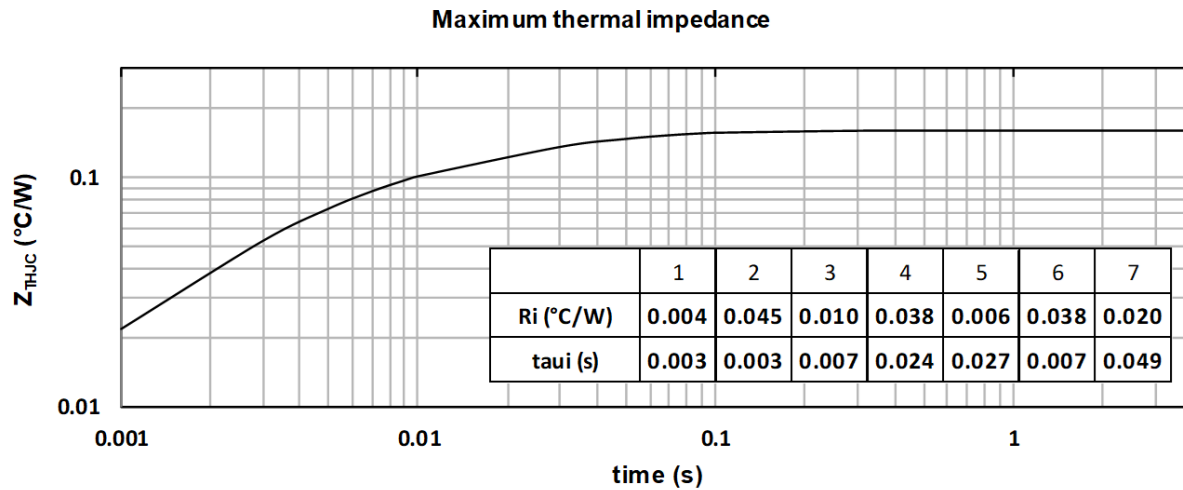


Figure 2 • Forward Current vs Forward Voltage

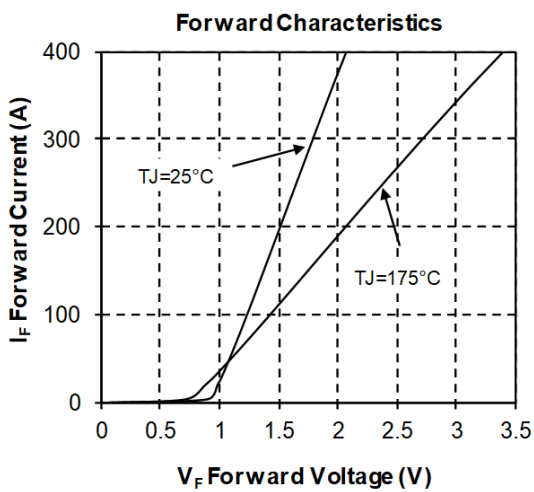
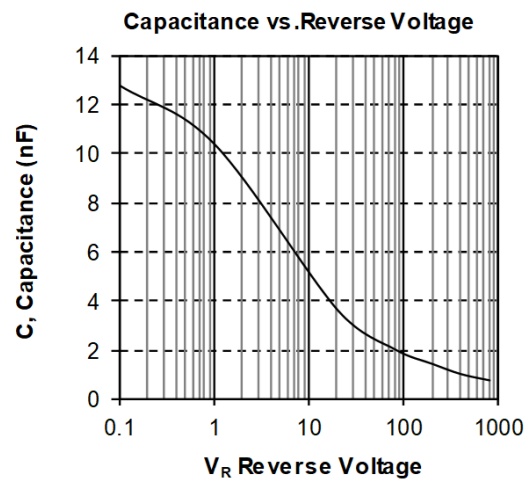


Figure 3 • Capacitance vs. Reverse Voltage



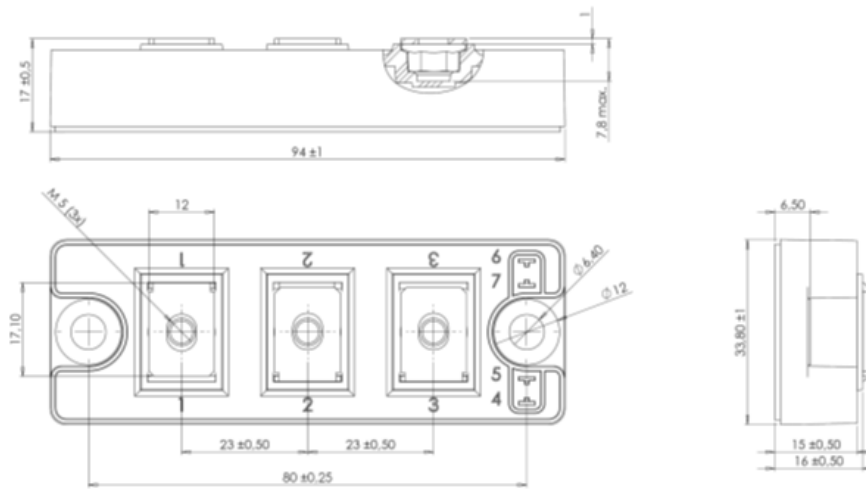
### 3 Package Specifications

This section shows the package specifications for the MSCDC200A120D1PAG device.

#### 3.1 Package Outline Drawing

This section shows the package outline drawing of the MSCDC200A120D1PAG device. The dimensions in the following figure are in millimeters.

**Figure 4 • Package Outline Drawing**



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